Switching diode

UMN10N

●Applications

Very fast recovery

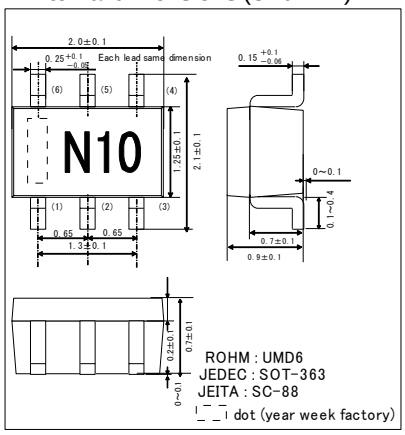
●Features

1) Small mold type. (UMD6)
2) High reliability

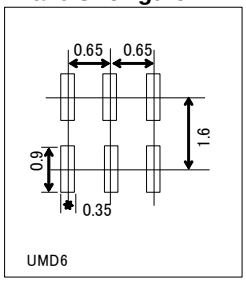
●Construction

Silicon epitaxial planer

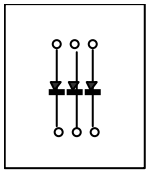
●External dimensions (Unit : mm)



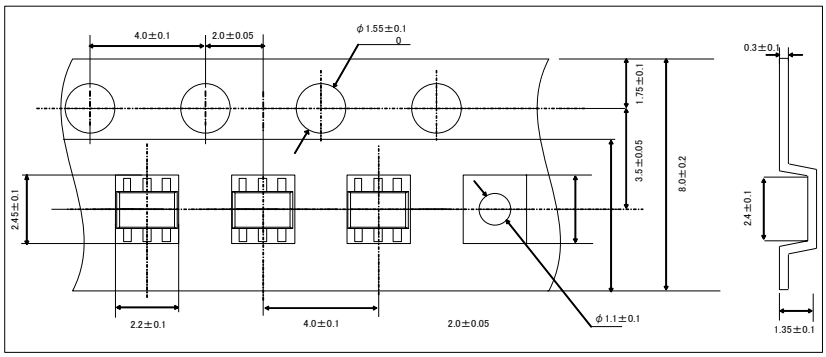
●Land size figure



●Structure



●Taping dimensions (Unit : mm)



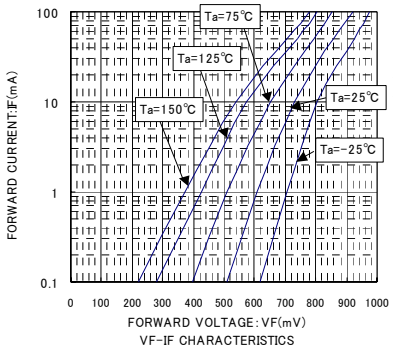
●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive peak)	V_{RM}	80	V
Reverse voltage (DC)	V_R	80	V
Forward current repetitive peak (Single)	I_{FM}	300	mA
Average rectified forward current (Single)	Io	100	mA
Surge current (t=1us)	I_{surge}	4	A
Power dissipation	Pd	200	mW
Junction temperature	Tj	150	℃
Storage temperature	Tstg	-55 to +150	℃

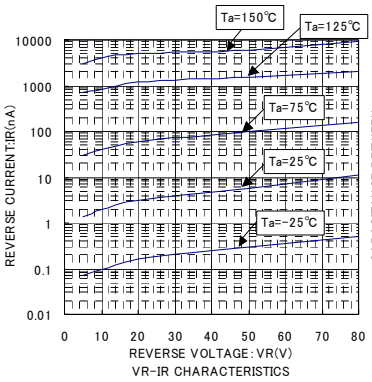
●Electrical characteristic (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	-	-	1.2	V	I_F=100mA
Reverse current	I_R	-	-	0.1	μA	V_R=70V
Capacitance between terminal	Ct	-	-	3.5	pF	V_R=6V , f=1MHz
Reverse recovery time	trr	-	-	4	ns	V_R=6V , IF=5mA , RL=50Ω

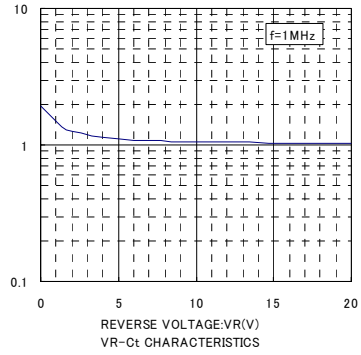
●Electrical characteristic curves



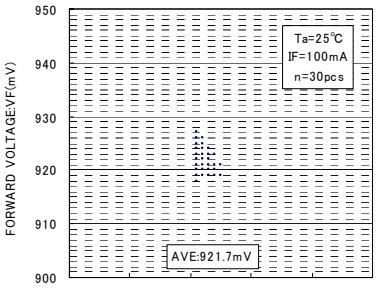
VF-IF CHARACTERISTICS



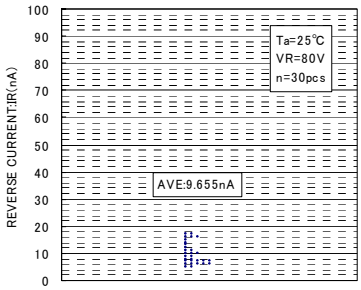
VR-IR CHARACTERISTICS



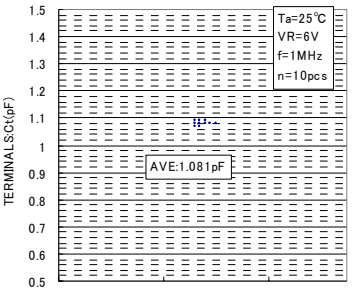
VR-Ct CHARACTERISTICS



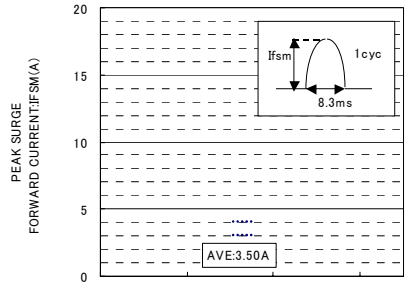
VF DISPERSION MAP



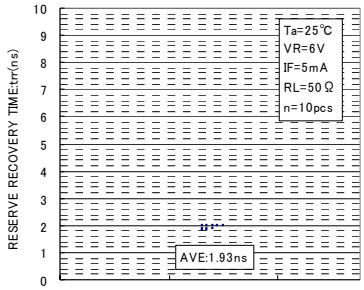
IR DISPERSION MAP



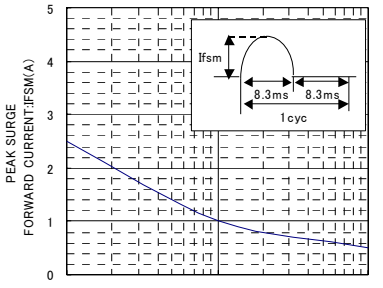
Ct DISPERSION MAP



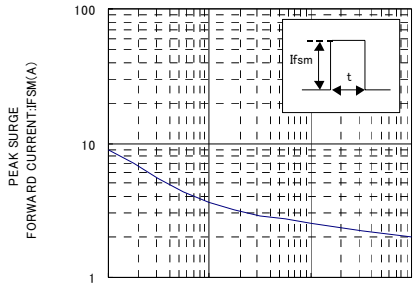
IFSM DISRESION MAP



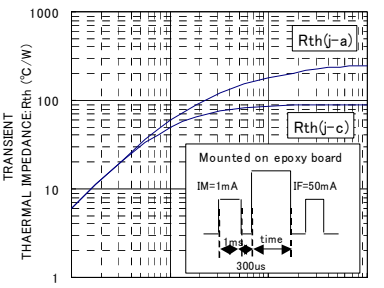
trr DISPERSION MAP



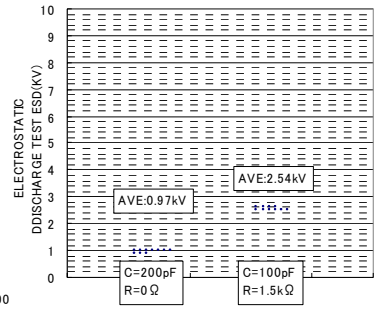
IFSM-CYCLE CHARACTERISTICS



IFSM-t CHARACTERISTICS



Rth-t CHARACTERISTICS



ESD DISPERSION MAP

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